

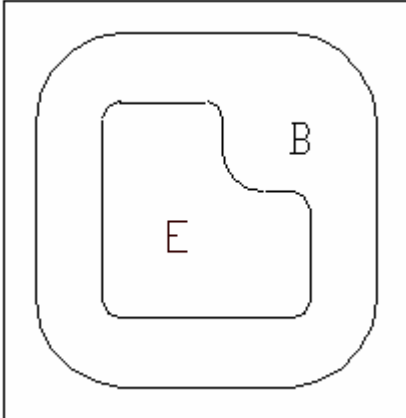
C1815 Silicon NPN Epitaxial Transistor

Description : The C1815 is designed for audio frequency general purpose amplifier applications and driver stage amplifier applications

Features: ●Excellent h_{FE} Linearity

●Complementary to A1015

Chip Appearance

	Chip Size		350um × 350um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	110um × 110um
		Emitter	100um × 100um
	Front Metal		Al
	Backside Metal		Au(As)
	Scribe line width		40um
	Wafer Size		6 inch

Electrical Characteristics($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$		0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$		0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=0.1\text{mA}$,	60		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=1\text{mA}$,	50		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=0.1\text{mA}$,	5.0		V
DC Current Gain	h_{FE}	$V_{CE}=6\text{V}, I_C=2\text{mA}$	150	600	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		0.30	V